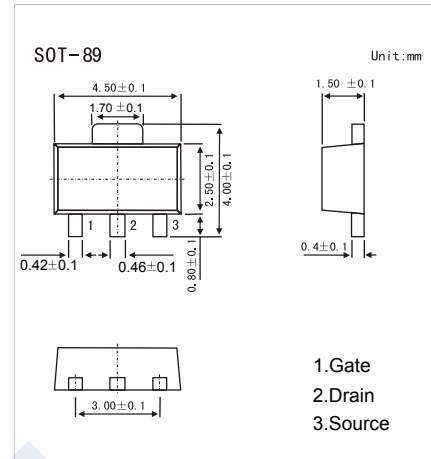
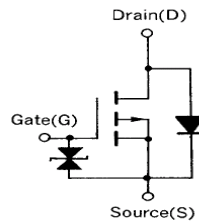


P-Channel MOSFET

2SJ212

■ Features

- V_{DS} (V) = -60V
- I_D = -500m A
- $R_{DS(ON)} < 3 \Omega$ ($V_{GS} = -10V$)
- $R_{DS(ON)} < 4 \Omega$ ($V_{GS} = -4V$)



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	-0.5	A
Pulsed Drain Current (Note.1)	I_{DM}	-1	
Power Dissipation	P_D	2	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Junction Storage Temperature Range	T_{stg}	-55 to 150	

Note.1: $PW \leq 10\text{ms}$, Duty Cycle $\leq 50\%$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

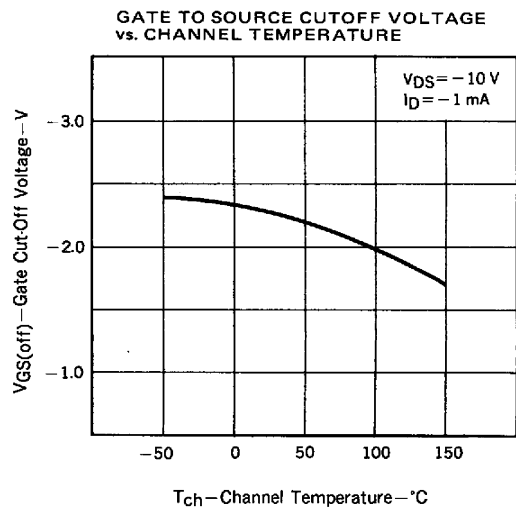
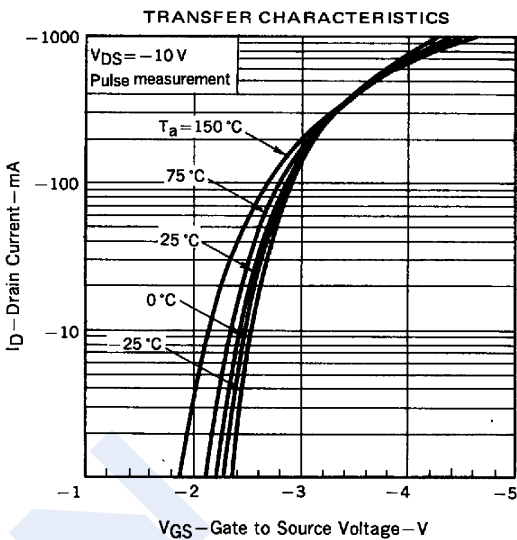
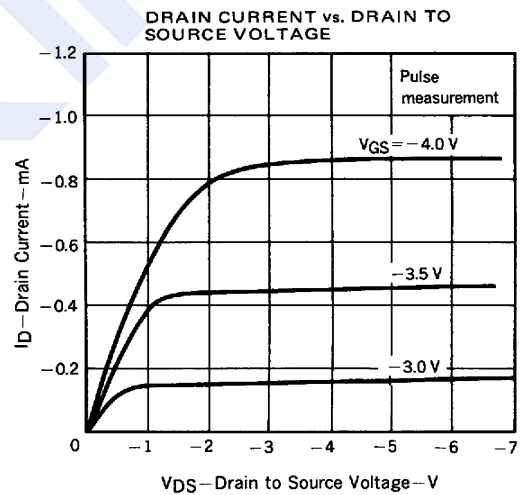
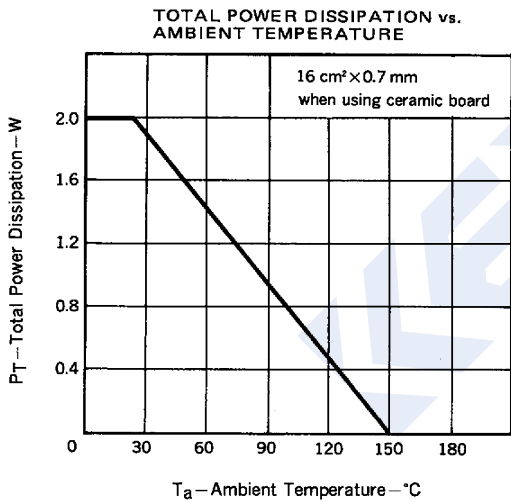
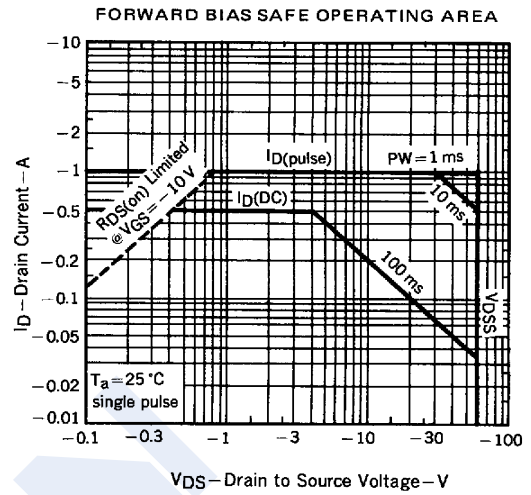
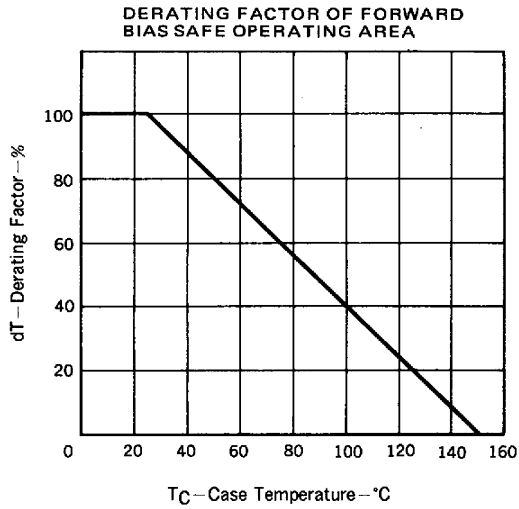
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D = -250 \mu\text{A}$, $V_{GS} = 0V$	-60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60V$, $V_{GS} = 0V$			-10	μA
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0V$, $V_{GS} = \pm 20V$			± 10	μA
Gate Cut off Voltage	$V_{GS(off)}$	$V_{DS} = -10V$, $I_D = -1\text{mA}$	-1		-3	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4V$, $I_D = -0.3A$			4	Ω
		$V_{GS} = -10V$, $I_D = -0.5A$			3	
Forward Transconductance	g_{FS}	$V_{DS} = -5V$, $I_D = -0.5A$	0.4	0.54		S
Input Capacitance	C_{iss}	$V_{GS} = 0V$, $V_{DS} = -5V$, $f = 1\text{MHz}$		160		pF
Output Capacitance	C_{oss}			100		
Reverse Transfer Capacitance	C_{rss}			25		
Turn-On DelayTime	$t_{d(on)}$				130	
Turn-On Rise Time	t_r	$V_{GS(on)} = -4V$, $V_{DS} = -5V$, $I_D = -0.3A$, $R_L = 1.5 \Omega$, $R_{GEN} = 10 \Omega$		380		
Turn-Off DelayTime	$t_{d(off)}$			95		
Turn-Off Fall Time	t_f			140		

■ Marking

Marking	PO
---------	----

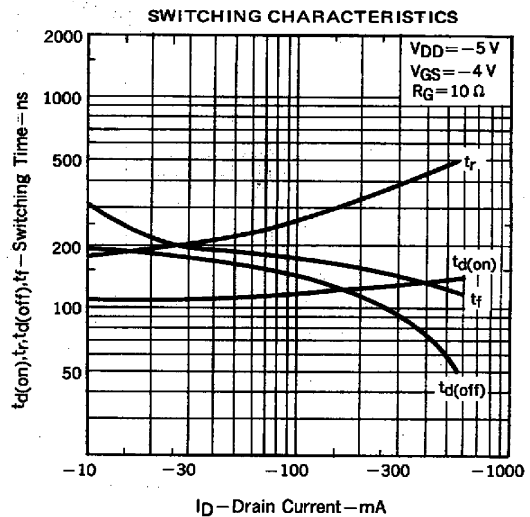
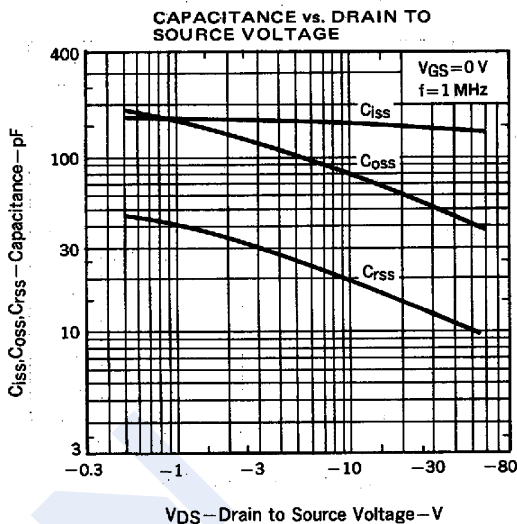
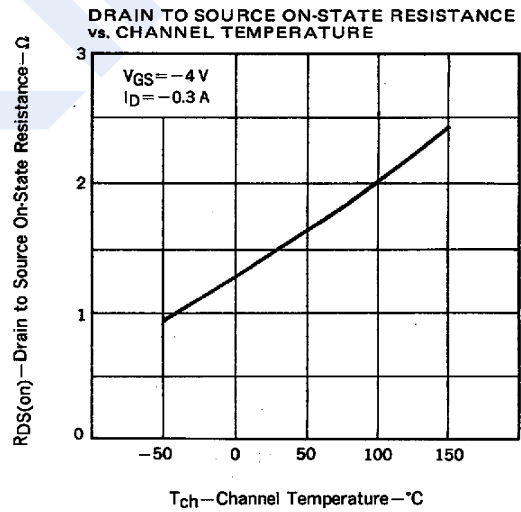
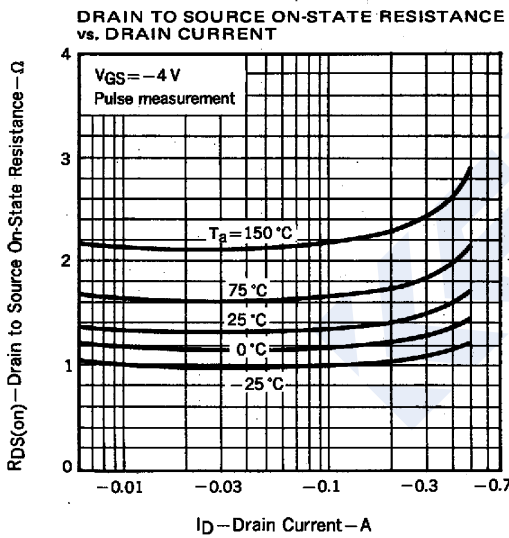
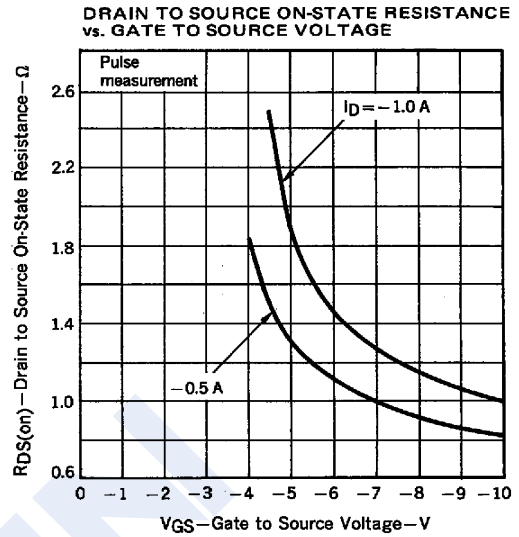
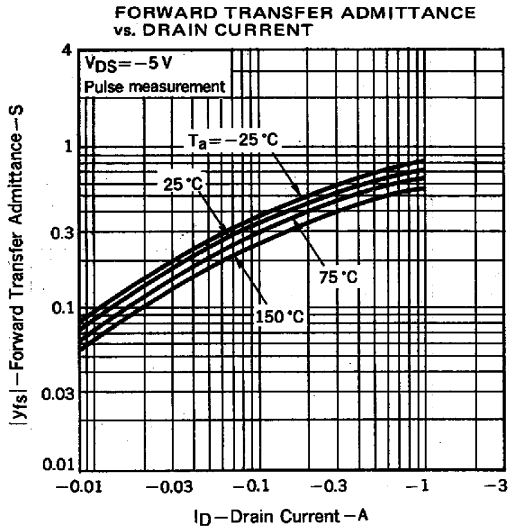
P-Channel MOSFET 2SJ212

■ Typical Characteristics



P-Channel MOSFET 2SJ212

■ Typical Characteristics



P-Channel MOSFET

2SJ212

■ Typical Characteristics

